| 4237 Claser near3 ablat\$3) same (via hole open\$4 trench contact) Claser near3 ablat\$3) same (via hole open\$4 trench contact) Claser near3 ablat\$3) Claser near3 ablat\$3] Claser near3 ablat\$3] Claser near3 abla | L Number | u:+c | Search Text | DB | Time stamp |
|---|----------|-------|--|--|------------------|
| Crench contact) 10 ((laser near3 ablat\$3) same (via hole open\$4 trench contact)) and (part) 1392 1393 1394 1394 1395 13 | | | | | |
| 107 ((liaser near3 ablat3)) amme (via hole open\$4 US-PGUB US | ا | 123, | | | 2004/00/00 11:33 |
| trench contact) and (TFT (thin nears film US-FGFUB 1392 ((laser near3 ablat3) same (via hole open\$4 USPAT; USPAT | 4 | 107 | | | 2004/06/08 14:35 |
| | | | | , | |
| trench contact) and isolates3 us-FGPUB us-FGPUB copen\$4 trench contact) and isolates3 us-FGPUB us- | . ` | | near5 transistor)) | | |
| 155 (((laser near3 ablat\$3) same (via hole open\$4 trench contact)) and (ref (thin near5 film near5 transistor)) ((laser near3 ablat\$3) same (via hole open\$4 trench contact)) ((laser near3 ablat\$3) same (via hole open\$4 trench contact)) ((laser near3 ablat\$3) same (via hole open\$4 trench contact) (laser near3 ablat\$3) same (via hole open\$4 trench contact) (laser near3 ablat\$3) same (via hole open\$4 trench contact) (laser near3 ablat\$3) same (via hole open\$4 trench contact) (laser near3 ablat\$3) same (via hole open\$4 trench contact) ((laser near3 ablat\$3) same (via hole open\$4 trench contact) ((laser near3 ablat\$3) same (via hole open\$4 trench contact) ((laser near3 ablat\$3) and (via hole open\$4 trench contact) ((laser near3 ablat\$3) ame (via hole open\$4 trench contact)) ((laser near3 ablat\$3) ame (via hole open\$4 trench contact)) ((laser near3 ablat\$3) ame (via hole open\$4 trench contact)) ((laser near3 ablat\$3) ame (via hole open\$4 trench contact)) ((laser near3 ablat\$3) ame (via hole open\$4 trench contact)) ((laser near3 ablat\$3) ame (via hole open\$4 trench contact)) ((laser near3 ablat\$3) ame (via hole open\$4 trench contact)) ((laser near3 ablat\$3) ame (via hole open\$4 trench contact)) ((laser near5 ablat\$3) ame (via hole open\$4 trench contact)) ((laser near5 film near5 transistor)) (USPAT; USPAT; undersold film near5 film near5 transistor)) (USPAT; undersold film near5 film near5 transistor)) (USPAT; undersold film near5 film near5 transistor)) ((loser near6) (loser near6 ablat\$3) ((loser near6) (loser near6) | 5 | 1392 | ((laser near3 ablat\$3) same (via hole open\$4 | USPAT; | 2004/06/08 14:34 |
| Open84 trench contact) and isolate(3) US-PGPUB US-PGPUB Compensation that it is the compensation open84 trench contact) and (FFT (thin nears film nears film nears transistor)) and ((((laser near) ablate(3)) ame ((via hole open84 trench contact)) and isolate(3)) ame (via hole open84 trench contact) Sil (laser near) ablate(3) ame (via hole open84 trench contact) Compensation trench contact) | | | | | |
| (device mear5 isolats3) | 6 | 155 | | • | 2004/06/08 14:34 |
| 5 | | ŀ | | US-PGPUB | |
| OpenS4 trench contact) and (ITFT (thin near5 film near5 transistor)) and (IC() aser near3 ablat\$3) same (via hole open\$4 trench contact)) and isolat\$3) and (device near5 isolat\$3)) | | _ | , | ,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,, | 2001/05/00 11 01 |
| ### ### #### #### #################### | ′ | 5 | | | 2004/06/08 14:34 |
| ablat33) same (via hole open\$4 trench contact)) and isolat\$3) and (device near's isolat\$31) (laser near3 ablat\$3) same (via hole open\$4 trench contact) (laser near3 ablat\$3) and (via hole open\$4 trench contact) ((laser near3 ablat\$3) same (via hole open\$4 trench contact) ((laser near3 ablat\$3) same (via hole open\$4 trench contact) ((laser near3 ablat\$3) same (via hole open\$4 trench contact) ((laser near3 ablat\$3) same (via hole open\$4 trench contact)) ((laser near3 ablat\$3) and (via hole open\$4 trench contact) ((laser near3 ablat\$3) same (via hole open\$4 trench contact) ((laser near3 ablat\$3) and (via hole open\$4 trench contact) ((laser near3 ablat\$3) same (via hole open\$4 trench contact) (laser near3 ablat\$3) and (via hole open\$4 trench contact) ((laser near3 ablat\$3) same (via hole open\$4 trench contact) ((laser near3 ablat\$3) same (via hole open\$4 trench contact) ((laser near3 ablat\$3) same (via hole open\$4 trench contact) ((laser near3 ablat\$3) same (via hole open\$4 trench contact) ((laser near3 ablat\$3) same (via hole open\$4 trench contact) ((laser near3 ablat\$3) same (via hole open\$4 trench contact) ((laser near3 ablat\$3) same (via hole open\$4 trench contact) ((laser near3 ablat\$3) same (via hole open\$4 trench contact) ((laser near3 ablat\$3) same (via hole open\$4 trench contact) ((laser near3 ablat\$3) same (via hole open\$4 trench contact) ((laser near3 ablat\$3) ((laser near3 ablat\$3) ((laser near3 ablat\$3) | | | | US-PGPUB | |
| contact) and isolat\$3) and (device nears isolat\$3) (laser near3 ablat\$3) same (via hole open\$4 EPO; JFO; DERWENT; LEM_TDB (laser near3 ablat\$3) same (via hole open\$4 EPO; JFO; DERWENT; LEM_TDB (laser near3 ablat\$3) same (via hole open\$4 EPO; JFO; DERWENT; LEM_TDB (laser near3 ablat\$3) same (via hole open\$4 EPO; JFO; DERWENT; LEM_TDB (laser near3 ablat\$3) same (via hole open\$4 EPO; JFO; DERWENT; LEM_TDB ERWENT; LEM_TDB ER | | | | | |
| Solution | | | | | |
| | | | | |] |
| 1 1 1 1 1 1 1 1 1 1 | 8 | 350 | (laser near3 ablat\$3) same (via hole open\$4 | EPO; JPO; | 2004/06/08 14:35 |
| 1 | | | trench contact) | DERWENT; | |
| trench contact) ((laser near3 ablat\$3) same (via hole open\$4 trench contact)) ((laser near3 ablat\$3) and (via hole open\$4 trench contact)) ((laser near3 ablat\$3) and (via hole open\$4 trench contact)) ((laser near3 ablat\$3) same (via hole open\$4 trench contact)) ((laser near3 ablat\$3) and (via hole open\$4 trench contact)) ((laser near3 ablat\$3) and (via hole open\$4 trench contact)) (laser near3 ablat\$3) and (via hole open\$4 trench contact)) - 28052 (TFT (thin near5 film near5 transistor)) - 1898 ((TFT (thin near5 film near5 transistor)) - 1899 ((TFT (thin near5 film near5 transistor)) - 1899 (((TFT (thin near5 film near5 transistor))) - 1894 (((TFT (thin near5 film near5 transistor))) - 1895 (((TFT (thin near5 film near5 transistor))) - 1896 (((TFT (thin near5 film near5 transistor))) - 1897 (((TFT (thin near5 film near5 transistor))) - 29 (((TFT (thin near5 film near5 transistor))) - 20 (((TFT (thin near5 film near5 transistor))) - 30 ((((TFT (thin near5 film near5 transistor))) - 31941 ((((TFT (thin near5 film near5 transistor))) - 31941 ((((TFT (thin near5 film near5 transistor))) - 31941 ((((IR near5 jet near5 print\$3))) - 31941 ((((IR near5 jet ne | | | | | |
| ((laser near3 ablat\$3) same (via hole open\$4 trench contact)) ((laser near3 ablat\$3) and (via hole open\$4 trench contact)) ((laser near3 ablat\$3) and ((laser near3 ablat\$3) and ((laser near3 ablat\$3)) and ((laser near3 ablat\$3)) same (via hole open\$4 trench contact)) ((laser near3 ablat\$3) and (via hole open\$4 trench contact)) ((laser near3 ablat\$3) and (via hole open\$4 trench contact)) ((laser near5 ablat\$3) and (via hole open\$4 trench contact)) and (TFT (thin near5 film near5 transistor)) - 28052 ((TFT (thin near5 film near5 transistor)) (USPAT; US-PGPUB USPAT; US- | 9 | 531 | | 1 | 2004/06/08 14:35 |
| ((laser near3 ablat\$3) same (via hole open\$4 rench contact)) ((laser near3 ablat\$3) and ((laser near3 ablat\$3) and ((laser near3 ablat\$3)) and ((laser near3 ablat\$3)) and (via hole open\$4 trench contact)) ((laser near3 ablat\$3) and (via hole open\$4 trench contact)) ((laser near3 ablat\$3)) and (via hole open\$4 trench contact)) ((laser near3 ablat\$3)) and (via hole open\$4 trench contact)) (laser near3 ablat\$3) and (via hole open\$4 trench contact)) and (TFT (thin near5 film near5 film near5 film rear5 film rear5 film rear5 film rear5 film near5 fi | | | trench contact) | 1 | |
| trench contact)) ((laser near3 ablat53) and (via hole open\$4 trench contact)) 1 (((laser near3 ablat53) same (via hole open\$4 trench contact)) 1 (((laser near3 ablat53) same (via hole open\$4 trench contact)) and (TFT (thin near5 film near5 transistor)) 2 ((TFT (thin near5 film near5 transistor)) 2 (TFT (thin near5 film near5 transistor)) 2 ((TFT (thin near5 film near5 transistor))) 2 ((TFT (thin near5 film near5 transistor))) 3 ((TFT (thin near5 film near5 transistor))) 4 ((TFT (thin near5 film near5 transistor))) 5 ((TFT (thin near5 film near5 transistor))) 6 ((TFT (thin near5 film near5 transistor))) 7 ((TFT (thin near5 film near5 transistor))) 8 ((TFT (thin near5 film near5 transistor))) 9 ((TFT (thin near5 film near5 transistor))) 1 ((TFT (thin near5 film near5 transistor))) 1 (TFT (thin near5 film near5 transistor)) 1 (TFT (thin near5 film near5 transistor)) 1 (TFT (thin near5 film near5 transistor)) 1 (TFT (thin near5 print\$3) and (source and drain)) and (laser near5 ablat\$3)) 2 (TFT (thin near5 film near5 film near5 transistor)) 3 (TFT (thin near5 film near5 transistor)) 4 (TFT (thin near5 film near5 transistor)) 5 (TFT (thin near5 film near5 transistor)) 6 (TFT (thin near5 film near5 transistor)) 7 (TFT (thin near5 film near5 transistor)) 8 (TFT (thin near5 film near5 transistor)) 9 (TFT (thin near5 film near5 transistor)) 1 (TF | 10 | E 3 1 | //lagon noama ablatéa) / hala | _ | 2004/05/00 24 55 |
| (via hole open§4 trench contact) | ** | 531 | | 1 | 2004/06/08 14:35 |
| 1 |] | | | | |
| Open§4 trench contact) ((laser near3 ablat\$3) and (via hole open§4 trench contact)) and (TFT (thin near5 film near5 transistor)) USPAT; US | 11 | 1 | | | 2004/06/08 14.35 |
| ablat\$3) and (via hole open\$4 trench contact)) and (TFT (thin near5 film near5 transistor)) - 28052 (TFT (thin near5 film near5 transistor)) 1898 ((TFT (thin near5 film near5 transistor)) and (solution near10 process\$3) - 1592 (((TFT (thin near5 film near5 transistor))) and (solution near10 process\$3)) and pattern\$4 - 799 ((((TFT (thin near5 film near5 transistor))) and (solution near10 process\$3)) and pattern\$4 - (((((TFT (thin near5 film near5 transistor))) and (solution near10 process\$3)) and pattern\$4 ((((((TFT (thin near5 film near5 transistor)))) and (solution near10 process\$3)) and pattern\$4) and (dielectric inuslat\$3) and (laser near5 ablat\$3) - 24 ((((((TFT (thin near5 film near5 transistor))) process\$3)) and pattern\$4) and (dielectric inuslat\$3)) and (laser near5 ablat\$3) - 14 ((((((TFT (thin near5 film near5 transistor))) process\$3)) and pattern\$4) and (dielectric inuslat\$3)) and (laser near5 ablat\$3)) - 1715 ((ink near5 jet near5 print\$3) and (source and drain) and (TFT (thin near5 film near5 transistor)) - 40 (((ink near5 jet near5 print\$3) and (source and drain)) and (TFT (thin near5 film near5 transistor)) - 40 (((ink near5 film near5 transistor))) and (solution and process\$3)) and pattern\$4 - 1715 (((TFT (thin near5 film near5 transistor))) and (solution and process\$3)) and pattern\$4 - 1715 (((TFT (thin near5 film near5 transistor))) and (solution and process\$3)) and pattern\$4 - 1715 (((TFT (thin near5 film near5 transistor))) and (solution and process\$3)) and pattern\$4 - 1716 (((TFT (thin near5 film near5 transistor))) and (solution and process\$3)) and pattern\$4 - 1716 (((TFT (thin near5 film near5 transistor))) and (solution and process\$3)) and pattern\$4 - 1716 (((TFT (thin near5 film near5 transistor))) and (solution and process\$3)) and pattern\$4 - 1716 (((TFT (thin near5 film near5 transistor))) perwent; perputation and process\$3) and pattern\$4 - 1717 (THIN near5 film near5 transistor)) perwent; perputation and process\$3) and pattern\$4 - 1717 (THIN near5 film near5 transis | - | _ | | | 2001,00,00 14.35 |
| Contact) and (TFT (thin near5 film near5 transistor) USPAT; US-PGPUB USPAT; | | | | | |
| 28052 (TFT (thin near5 film near5 transistor)) | | | contact))) and (TFT (thin near5 film near5 | _ | |
| 1898 | | | | | |
| 1898 | - | 28052 | (TFT (thin near5 film near5 transistor)) | • | 2004/06/08 14:33 |
| and (solution near10 process\$3) ((((TFT (thin near5 film near5 transistor))) and (solution near10) process\$3)) and pattern\$4 799 (((((TFT (thin near5 film near5 transistor))) and (solution near10 process\$3)) and pattern\$4) and (solution near10) pattern\$4] ((((((TFT (thin near5 film near5 transistor))) and (solution near10) process\$3)) and pattern\$4) and (dielectric inuslat\$3)) and (laser near5 ablat\$3) ((((((TFT (thin near5 film near5) transistor))) and (solution near10) process\$3)) and pattern\$4) and (dielectric inuslat\$3)) and (laser near5 ablat\$3) ((((((TFT (thin near5 film near5) transistor))) and (solution near10) process\$3)) and pattern\$4) and (dielectric inuslat\$3)) and (laser near5 ablat\$3) (((((TFT (thin near5 film near5) transistor))) and (solution near10) process\$3)) and pattern\$4) and (dielectric inuslat\$3)) and (laser near5 ablat\$3)) and (spin near5 coat\$3) ink near5 jet near5 print\$3 and (source and drain) (((ink near5 jet near5 print\$3)) and (source and drain)) and ((TFT (thin near5 film near5 transistor)) 491 ((((ink near5 jet near5 print\$3)) and (source and drain)) and ((TFT (thin near5 film near5 transistor))) ((((((TFT (thin near5 film near5 transistor))) and (solution and process\$3) (((((((((((((((((((((((((((((((((((| | 1000 | //MDM /this sour film sour two-sistem))) | | |
| 1592 (((TFT (thin near5 film near5 transistor))) and (solution near10 process\$3)) and pattern\$4 (((TFT (thin near5 film near5 transistor))) uspAT; us-pGpUB uspAT; | - | 1090 | | , | 2004/05/24 11:31 |
| and (solution near10 process\$3)) and pattern\$4 ((((TFT (thin near5 film near5 transistor))) and (solution near10 process\$3)) and pattern\$4 and (dielectric inuslat\$3) (((((TFT (thin near5 film near5 transistor))) and (solution near10 process\$3)) and pattern\$4) and (dielectric inuslat\$3)) and (laser near5 ablat\$3) ((((((TFT (thin near5 film near5) ((((((TFT (thin near5 film near5) transistor)))) and (solution near10 process\$3)) and pattern\$4) and (dielectric inuslat\$3)) and (laser near5 ablat\$3)) and (spin near5 coat\$3) and pattern\$4) and (dielectric inuslat\$3)) and (laser near5 ablat\$3)) and (spin near5 coat\$3) ink near5 jet near5 print\$3) and (source and drain) ((ink near5 jet near5 print\$3) and (source and drain)) and (TFT (thin near5 film near5 (US-PGPUB USPAT; US-PGPUB USPAT; US-P | _ | 1592 | | 1 | 2004/05/24 11.32 |
| pattern\$4 ((((TFT (thin near5 film near5 transistor))) and (solution near10 process\$3)) and pattern\$4) and (dielectric inuslat\$3) (((((TFT (thin near5 film near5 | | 1332 | | • | 2004/03/24 11:32 |
| and (solution near10 process\$3)) and pattern\$4) and (dielectric inuslat\$3) ((((TFT (thin near5 film near5 process\$3)) and pottern\$4) and (dielectric inuslat\$3)) 14 (((((TFT (thin near5 film near5 process\$3)) and pattern\$4) and (dielectric inuslat\$3)) and (laser near5 ablat\$3) ((((((TFT (thin near5 film near5 process\$3)) and pattern\$4) and (dielectric inuslat\$3)) and (laser near5 ablat\$3)) and (spin near5 coat\$3) 1378 (ink near5 jet near5 print\$3) and (source inuslat\$3)) and (laser near5 ablat\$3)) and (spin near5 coat\$3) (ink near5 jet near5 print\$3) and (source ind drain)) and (TFT (thin near5 film near5 ind near5 ind near5 print\$3) and (source ind drain)) and (TFT (thin near5 film near5 ind near5 ind near5 ind near5 ind in near5 ind in near5 ind (source ind drain)) and (TFT (thin near5 film near5 ind in near5 ind in near5 ind (source ind drain)) and (source ind drain)) and (source ind drain) and (source ind drain) and (source ind drain) and (source ind drain)) and (source ind drain) ind (so | | | | 05 10105 | |
| and (solution near10 process\$3)) and pattern\$4) and (dielectric inuslat\$3) ((((((TFT (thin near5 film near5 process\$3)) and pattern\$4) and (dielectric inuslat\$3)) ((((((TFT (thin near5 film near5 process\$3)) and pattern\$4) and (dielectric inuslat\$3)) and (laser near5 ablat\$3) ((((((TFT (thin near5 film near5 transistor))) and (solution near10 process\$3)) and pattern\$4) and (dielectric inuslat\$3)) and (laser near5 ablat\$3)) and (spin near5 coat\$3) 1378 (ink near5 jet near5 print\$3) and (source and drain) and (TFT (thin near5 film near5 (laser near5 ablat\$3)) (((ink near5 jet near5 print\$3)) and (source and drain)) and (TFT (thin near5 film near5 (laser near5 ablat\$3)) (((ink near5 jet near5 print\$3)) and (source and drain)) and (TFT (thin near5 film near5 (laser near5 ablat\$3)) (((ink near5 jet near5 print\$3)) and (source and drain)) and (laser near5 ablat\$3) ((((TFT (thin near5 film near5 transistor))) ((((TFT (thin near5 film near5 transistor)))) and (solution and process\$3)) and (solution and process\$3)) and pattern\$4 ((((TFT (thin near5 film near5 transistor)))) and (solution and process\$3)) and pattern\$4 (((((TFT (thin near5 film near5 transistor)))) and (solution and process\$3)) and pattern\$4 (((((TFT (thin near5 film near5 transistor)))) and (solution and process\$3)) and pattern\$4 (((((TFT (thin near5 film near5 transistor)))) and (solution and process\$3)) and pattern\$4 (((((TFT (thin near5 film near5 transistor)))) and (solution and process\$3)) and pattern\$4 (((((TFT (thin near5 film near5 transistor)))) and (solution and process\$3)) and pattern\$4 (((((TFT (thin near5 film near5 transistor)))) and (solution and process\$3)) and pattern\$4 (((((TFT (thin near5 film near5 transistor)))) and (solution and process\$3)) and pattern\$4 (((((((((((((((((((((((((((((((((((| - | 799 | ((((TFT (thin near5 film near5 transistor))) | USPAT; | 2004/05/24 11:21 |
| 24 | | | | US-PGPUB | |
| transistor)) and (solution near10 process\$3)) and pattern\$4) and (dielectric inuslat\$3)) and (laser near5 ablat\$3) | | | | | |
| process\$3) and pattern\$4) and (dielectric inuslat\$3) and (laser near5 ablat\$3) USPAT; USPAT; US-PGPUB USPAT; US-PG | - | 24 | | • | 2004/05/24 11:32 |
| inuslat\$3) and (laser near5 ablat\$3) (((((TFT (thin near5 film near5 transistor))) and (solution near10 process\$3)) and pattern\$4) and (dielectric inuslat\$3) and (laser near5 ablat\$3)) and (spin near5 coat\$3) ink near5 jet near5 print\$3 (ink near5 jet near5 print\$3) and (source and drain) ((ink near5 jet near5 print\$3) and (source and drain)) and (TFT (thin near5 film near5 transistor)) (((ink near5 jet near5 print\$3)) and (source and drain)) and (TFT (thin near5 film near5 transistor)) (((ink near5 jet near5 print\$3)) and (source and drain)) and (TFT (thin near5 film near5 transistor)) (((ink near5 jet near5 print\$3)) and (source and drain)) and (TFT (thin near5 film near5 transistor)) (((ink near5 jet near5 print\$3)) and (source and drain)) and (TFT (thin near5 film near5 transistor)) (((ink near5 jet near5 print\$3)) and (source and drain)) and (source and drain)) and (source and drain) and (source and (source and drain) and (source and drain) and (source and (source and drain) and (source and (source and drain) and (source and (so | | | | US-PGPUB | |
| 14 | | | | | |
| transistor))) and (solution near10 process\$3)) and pattern\$4) and (dielectric inuslat\$3)) and (laser near5 ablat\$3)) and (spin near5 coat\$3) ink near5 jet near5 print\$3 (ink near5 jet near5 print\$3) and (source and drain) ((ink near5 jet near5 print\$3) and (source and drain)) and (TFT (thin near5 film near5 transistor)) (((ink near5 jet near5 print\$3)) and (source and drain)) and (TFT (thin near5 film near5 transistor)) (((ink near5 jet near5 print\$3)) and (source and drain)) and (TFT (thin near5 film near5 transistor)) (((ink near5 jet near5 print\$3)) and (source and drain)) and (TFT (thin near5 film near5 transistor)) (((ink near5 jet near5 print\$3)) and (source and drain)) and (laser near5 ablat\$3) ((((TFT (thin near5 film near5 transistor))) and (solution and process\$3)) ((((TFT (thin near5 film near5 transistor))) and (solution and process\$3)) and pattern\$4 ((((TFT (thin near5 film near5 transistor))) and (solution and process\$3)) and pattern\$4 (((((TFT (thin near5 film near5 transistor)))) and (solution and process\$3)) and pattern\$4 ((((((TFT (thin near5 film near5 transistor)))) and (solution and process\$3)) and pattern\$4 (((((((((((((((((((((((((((((((((((| _ | 14 | (((((TFT (thin near5 film near5 | USPAT. | 2004/05/24 11.28 |
| process\$3)) and pattern\$4) and (dielectric inuslat\$3)) and (laser near5 ablat\$3)) and (spin near5 coat\$3) 1378 (ink near5 jet near5 print\$3) and (source and drain) ((ink near5 jet near5 print\$3)) and (source and drain) and (TFT (thin near5 film near5 transistor)) (((ink near5 jet near5 print\$3)) and (source and drain)) and (TFT (thin near5 film near5 transistor)) (((ink near5 jet near5 print\$3)) and (source and drain)) and (TFT (thin near5 film near5 transistor)) (((ink near5 jet near5 print\$3)) and (source and drain)) and (TFT (thin near5 film near5 transistor)) (((ink near5 jet near5 print\$3)) and (source and drain)) and (laser near5 ablat\$3) (((ink near5 jet near5 print\$3)) and (source and drain)) and (laser near5 ablat\$3) (((ink near5 jet near5 print\$3)) and (source and drain)) and (laser near5 ablat\$3) (((ink near5 jet near5 print\$3)) and (source and drain)) and (laser near5 ablat\$3) (((ink near5 jet near5 print\$3)) and (source and drain)) and (laser near5 transistor)) (((ink near5 jet near5 print\$3)) and (laser near5 print\$3) (((ink near5 jet near5 print\$3)) and (source and drain) (((ink near5 jet near5 print\$3)) and (source and drain) (((ink near5 jet near5 print\$3)) and (source and drain) (((ink near5 jet near5 print\$3)) and (source and drain) (((ink near5 jet near5 print\$3)) and (source and drain) (((ink near5 jet near5 print\$3)) and (source and drain) ((((ink near5 jet near5 print\$3)) and (source and drain) (((ink near5 jet near5 print\$3) and (source and drain) (((ink near5 jet near5 print\$3) and (source and drain) (((ink near5 jet near5 print\$3) and (source and drain) (((ink near5 jet near5 print\$3) and (source and drain) (((ink near5 jet near5 print\$3) and (source and drain) (((ink near5 jet near5 print\$3) and (source and drain) (((ink near5 jet near5 print\$3) and (source and drain) (((ink near5 jet near5 print\$3) and (source and drain) (((ink near5 jet near5 print\$3) and (source and (sourc | | | | | 2001,03,24 11.20 |
| inuslat\$3)) and (laser near5 ablat\$3)) and (spin near5 coat\$3) ink near5 jet near5 print\$3 | | | process\$3)) and pattern\$4) and (dielectric | | |
| 31941 ink near5 jet near5 print\$3 USPAT; US-PGPUB USPAT; U | | | inuslat\$3)) and (laser near5 ablat\$3)) and | | |
| 1378 | | | | | |
| 1378 | - | 31941 | ink near5 jet near5 print\$3 | • | 2004/05/24 11:34 |
| and drain) ((ink near5 jet near5 print\$3) and (source and drain)) and (TFT (thin near5 film near5 transistor)) (((ink near5 jet near5 print\$3) and (source and drain)) and (TFT (thin near5 film near5 transistor)) (((ink near5 jet near5 print\$3) and (source and drain)) and (TFT (thin near5 film near5 transistor)) and drain) and (TFT (thin near5 film near5 transistor)) ((TFT (thin near5 film near5 transistor)) ((TFT (thin near5 film near5 transistor))) and (solution and process\$3) (((TFT (thin near5 film near5 transistor))) and (solution and process\$3)) and pattern\$4 ((((TFT (thin near5 film near5 transistor)))) and (solution and process\$3)) and pattern\$4 (((((TFT (thin near5 film near5 transistor)))) and (solution and process\$3)) and pattern\$4 (((((TFT (thin near5 film near5 transistor)))) and (solution and process\$3)) and pattern\$4 (((((TFT (thin near5 film near5 transistor)))) and (solution and process\$3)) and pattern\$4 ((((TFT (thin near5 film near5 transistor)))) and (solution and process\$3)) and pattern\$4 ((((TFT (thin near5 film near5 transistor)))) and (solution and process\$3)) and pattern\$4 ((((TFT (thin near5 film near5 transistor)))) and (solution and process\$3)) ((((TFT (thin near5 film near5 transistor)))) and (solution and process\$3)) ((((TFT (thin near5 film near5 transistor)))) and (solution and process\$3)) ((((TFT (thin near5 film near5 transistor)))) and (solution and process\$3)) ((((TFT (thin near5 film near5 transistor)))) and (solution and process\$3)) ((((TFT (thin near5 film near5 transistor)))) and (solution and process\$3)) | <u> </u> | 1270 | (ink noors jot noors maintal) and (| | 0004/05/04 55 51 |
| 491 ((ink near5 jet near5 print\$3) and (source and drain)) and (TFT (thin near5 film near5 transistor)) 40 ((ink near5 jet near5 print\$3) and (source and drain)) and (TFT (thin near5 film near5 transistor)) 36555 (TFT (thin near5 film near5 transistor)) 454 ((TFT (thin near5 film near5 transistor))) 454 (((TFT (thin near5 film near5 transistor))) 454 (((TFT (thin near5 film near5 transistor))) 455 (((TFT (thin near5 film near5 transistor))) 456 ((((TFT (thin near5 film near5 transistor)))) 457 ((((TFT (thin near5 film near5 transistor)))) 458 ((((TFT (thin near5 film near5 transistor)))) 459 ((((TFT (thin near5 film near5 transistor)))) 450 ((((TFT (thin near5 film near5 transistor)))) 451 ((((TFT (thin near5 film near5 transistor)))) 452 (((((TFT (thin near5 film near5 transistor))))) 453 (((((TFT (thin near5 film near5 transistor))))) 454 (((((TFT (thin near5 film near5 transistor))))) 455 ((((((TFT (thin near5 film near5 transistor))))) 456 (((((((TFT (thin near5 film near5 transistor))))) 457 ((((((((((((((((((((((((((((((((((((| · | 13/8 | | • | 2004/05/24 11:34 |
| and drain)) and (TFT (thin near5 film near5 transistor)) (((ink near5 jet near5 print\$3) and (source and drain)) and (TFT (thin near5 film near5 transistor)) 36555 (TFT (thin near5 film near5 transistor)) ((TFT (thin near5 film near5 transistor))) and (solution and process\$3) 454 (((TFT (thin near5 film near5 transistor))) and (solution and process\$3)) and pattern\$4 ((((TFT (thin near5 film near5 transistor)))) and (solution and process\$3)) and pattern\$4 ((((TFT (thin near5 film near5 transistor)))) and (solution and process\$3)) and pattern\$4 (((((TFT (thin near5 film near5 transistor)))) and (solution and process\$3)) and pattern\$4 ((((TFT (thin near5 film near5 transistor)))) and (solution and process\$3)) and pattern\$4 ((((TFT (thin near5 film near5 transistor)))) and (solution and process\$3)) and pattern\$4) DERWENT; and (laser ablat\$3) | _ | 491 | | | 2004/05/24 11.20 |
| transistor)) (((ink near5 jet near5 print\$3) and (source and drain)) and (TFT (thin near5 film near5 transistor)) 36555 (TFT (thin near5 film near5 transistor)) 1715 ((TFT (thin near5 film near5 transistor))) and (solution and process\$3) 454 (((TFT (thin near5 film near5 transistor))) and (solution and process\$3)) and pattern\$4 (((TFT (thin near5 film near5 transistor))) and (solution and process\$3)) and pattern\$4 (((TFT (thin near5 film near5 transistor))) and (solution and process\$3)) and pattern\$4 (((TFT (thin near5 film near5 transistor))) and (solution and process\$3)) and pattern\$4 DERWENT; IBM_TDB EPO; JPO; DERWENT; IBM_TDB EPO; JPO; DERWENT; IBM_TDB 2004/05/24 11:32 DERWENT; IBM_TDB 2004/05/24 11:33 DERWENT; IBM_TDB TDB 1:29 2004/05/24 11:31 2004/05/24 11:32 DERWENT; IBM_TDB DERWENT; IBM_TDB TDB TDB TDB TDB TDB TDB TDB | | | | | 2004/05/24 11:29 |
| 40 (((ink near5 jet near5 print\$3) and (source and drain)) and (TFT (thin near5 film near5 transistor)) and (laser near5 ablat\$3) 36555 (TFT (thin near5 film near5 transistor)) 1715 ((TFT (thin near5 film near5 transistor))) and (solution and process\$3) 454 (((TFT (thin near5 film near5 transistor))) and (solution and process\$3)) and pattern\$4 (((TFT (thin near5 film near5 transistor))) and (solution and process\$3)) and pattern\$4 ((((TFT (thin near5 film near5 transistor))) and (solution and process\$3)) and pattern\$4 ((((TFT (thin near5 film near5 transistor))) and (solution and process\$3)) and pattern\$4 DERWENT; IBM_TDB EPO; JPO; DERWENT; IBM_TDB EPO; JPO; DERWENT; IBM_TDB EPO; JPO; DERWENT; IBM_TDB DERWENT; IBM_TDB EPO; JPO; DERWENT; IBM_TDB | | | transistor)) | | |
| and drain)) and (TFT (thin near5 film near5 transistor)) and (laser near5 ablat\$3) (TFT (thin near5 film near5 transistor)) ((TFT (thin near5 film near5 transistor))) EPO; JPO; DERWENT; IBM_TDB and (solution and process\$3) (((TFT (thin near5 film near5 transistor))) EPO; JPO; DERWENT; IBM_TDB ((((TFT (thin near5 film near5 transistor))) EPO; JPO; DERWENT; IBM_TDB ((((TFT (thin near5 film near5 transistor))) EPO; JPO; DERWENT; IBM_TDB ((((TFT (thin near5 film near5 transistor))) EPO; JPO; DERWENT; IBM_TDB ((((TFT (thin near5 film near5 transistor))) EPO; JPO; DERWENT; IBM_TDB and (solution and process\$3)) and pattern\$4) DERWENT; IBM_TDB | - | 40 | (((ink near5 jet near5 print\$3) and (source | USPAT; | 2004/05/24 11:29 |
| 36555 (TFT (thin near5 film near5 transistor)) EPO; JPO; DERWENT; IBM_TDB ((TFT (thin near5 film near5 transistor))) and (solution and process\$3) (((TFT (thin near5 film near5 transistor))) and (solution and process\$3)) and pattern\$4 (((TFT (thin near5 film near5 transistor))) and (solution and process\$3)) and pattern\$4 (((TFT (thin near5 film near5 transistor))) and (solution and process\$3)) and pattern\$4 and (laser ablat\$3) EPO; JPO; DERWENT; IBM_TDB EPO; JPO; DERWENT; IBM_TDB | | | and drain)) and (TFT (thin near5 film near5 | | |
| DERWENT; IBM_TDB EPO; JPO; DERWENT; IBM_TDB IBM_TDB | | | | | |
| 1715 ((TFT (thin near5 film near5 transistor))) and (solution and process\$3) 454 (((TFT (thin near5 film near5 transistor))) and (solution and process\$3)) and pattern\$4 (((TFT (thin near5 film near5 transistor))) and (solution and process\$3)) and pattern\$4 ((((TFT (thin near5 film near5 transistor))) and (solution and process\$3)) and pattern\$4) and (solution and process\$3)) and pattern\$4) DERWENT; and (laser ablat\$3) | - | 36555 | (TFT (thin near5 film near5 transistor)) | | 2004/05/24 11:31 |
| 1715 ((TFT (thin near5 film near5 transistor))) and (solution and process\$3) 454 (((TFT (thin near5 film near5 transistor))) and (solution and process\$3)) and pattern\$4 (((TFT (thin near5 film near5 transistor))) and (solution and process\$3)) and pattern\$4 ((((TFT (thin near5 film near5 transistor))) and (solution and process\$3)) and pattern\$4) and (solution and process\$3)) and pattern\$4) DERWENT; and (laser ablat\$3) | | İ | | | |
| and (solution and process\$3) 454 (((TFT (thin near5 film near5 transistor))) | _ | 1715 | ((TFT (thin near5 film near5 transistor))) | | 2004/05/24 33 32 |
| 454 (((TFT (thin near5 film near5 transistor))) and (solution and process\$3)) and pattern\$4 DERWENT; IBM_TDB ((((TFT (thin near5 film near5 transistor))) EPO; JPO; DERWENT; and (solution and process\$3)) and pattern\$4) DERWENT; and (laser ablat\$3) DERWENT; IBM_TDB | | 1713 | | | 2004/05/24 11:32 |
| 454 (((TFT (thin near5 film near5 transistor))) and (solution and process\$3)) and pattern\$4 DERWENT; IBM_TDB ((((TFT (thin near5 film near5 transistor))) EPO; JPO; DERWENT; and (solution and process\$3)) and pattern\$4) DERWENT; and (laser ablat\$3) DERWENT; IBM_TDB | | | (27247201 una processys) | | |
| and (solution and process\$3)) and pattern\$4 DERWENT; IBM_TDB ((((TFT (thin near5 film near5 transistor))) EPO; JPO; and (solution and process\$3)) and pattern\$4) DERWENT; and (laser ablat\$3) DERWENT; IBM_TDB | - | 454 | (((TFT (thin near5 film near5 transistor))) | | 2004/05/24 11:32 |
| 36 ((((TFT (thin near5 film near5 transistor))) EPO; JPO; and (solution and process\$3)) and pattern\$4) DERWENT; and (laser ablat\$3) IBM_TDB | | | | · | ,, |
| and (solution and process\$3)) and pattern\$4) DERWENT; and (laser ablat\$3) | | İ | • | IBM_TDB | |
| and (solution and process\$3)) and pattern\$4) DERWENT; and (laser ablat\$3) IBM_TDB | - | 36 | | | 2004/05/24 11:33 |
| | ļ | | | • | |
| 20mm High and C/0/04 2 25 00 PM | | l | | IBM_TDB | |

| - | 34570 | ink near5 jet near5 print\$3 | EPO; JPO; DERWENT; | 2004/05/24 11:34 |
|---|---------|--|---|------------------|
| - | 32 | (ink near5 jet near5 print\$3) and (source and drain) | IBM_TDB EPO; JPO; DERWENT; | 2004/05/24 11:35 |
| - | 816918 | print\$3 writ\$3 | IBM_TDB USPAT; US-PGPUB | 2004/05/24 12:27 |
| _ | 13221 | (print\$3 writ\$3) and (TFT (thin near5 film near5 transistor)) | USPAT; US-PGPUB | 2004/05/24 12:28 |
| - | 7402 | ((print\$3 writ\$3) and (TFT (thin near5 film near5 transistor))) and (laser near\$5 ablat\$3) | USPAT; US-PGPUB | 2004/05/24 12:28 |
| - | 4333 | <pre>(((print\$3 writ\$3) and (TFT (thin near5 film near5 transistor))) and (laser near\$5 ablat\$3)) and (source and drain)</pre> | USPAT; US-PGPUB | 2004/05/24 12:07 |
| - | 4277 | ((((print\$3 writ\$3) and (TFT (thin near5 film near5 transistor))) and (laser near\$5 | USPAT; US-PGPUB | 2004/05/24 12:07 |
| - | 498 | ablat\$3)) and (source and drain)) and gate (((((print\$3 writ\$3) and (TFT (thin near5 film near5 transistor))) and (laser near\$5 ablat\$3)) and (source and drain)) and gate) and (ink near5 jet) | USPAT; US-PGPUB | 2004/05/24 12:07 |
| - | 485 | <pre>((((((print\$3 writ\$3) and (TFT (thin near5 film near5 transistor))) and (laser near\$5 ablat\$3)) and (source and drain)) and gate)</pre> | USPAT; US-PGPUB | 2004/05/24 12:08 |
| - | 1218286 | and (ink near5 jet)) and pattern\$4 print\$3 writ\$3 | EPO; JPO; DERWENT; | 2004/05/24 12:28 |
| - | 1324 | (print\$3 writ\$3) and (TFT (thin near5 film near5 transistor)) | IBM_TDB EPO; JPO; DERWENT; IBM TDB | 2004/05/24 12:28 |
| - | 77 | ((print\$3 writ\$3) and (TFT (thin near5 film near5 transistor))) and (laser near\$5 ablat\$3) | EPO; JPO; DERWENT; IBM TDB | 2004/05/24 12:28 |
| - | 28319 | (TFT (thin near5 film near5 transistor)) | USPAT; US-PGPUB | 2004/06/07 12:23 |
| - | 441 | ((TFT (thin near5 film near5 transistor))) and (laser near5 ablat\$6) | USPAT; US-PGPUB | 2004/06/07 12:24 |
| - | 68 | (((TFT (thin near5 film near5 transistor))) and (laser near5 ablat\$6)) and isolation | USPAT; US-PGPUB | 2004/06/07 12:42 |
| - | 4702 | | USPAT; US-PGPUB | 2004/06/07 12:43 |
| - | 235 | ((TFT (thin near5 film near5 transistor))) and ((laser near5 ablat\$3) same (pattern\$4 etch\$3)) | USPAT; US-PGPUB | 2004/06/07 14:40 |
| - | 0 | ((channel near3 length) with ("5" adj3 micoron)) | USPAT; US-PGPUB | 2004/06/07 15:31 |
| - | 1 | ("6602790").PN. | USPAT; US-PGPUB | 2004/06/07 19:58 |
| - | 28319 | (TFT (thin near5 film near5 transistor)) | USPAT; US-PGPUB | 2004/06/07 19:59 |
| - | 415 | ((TFT (thin near5 film near5 transistor))) and (laser near3 ablat\$3) | USPAT; US-PGPUB | 2004/06/07 20:24 |
| - | 178 | (((TFT (thin near5 film near5 transistor))) and (laser near3 ablat\$3)) and (STI isolat\$3) | USPAT; US-PGPUB | 2004/06/07 20:00 |
| - | 3559 | (laser near3 ablat\$3) same (via hole trench open\$3 groove recess) | USPAT; US-PGPUB | 2004/06/07 20:24 |
| - | 2240 | (laser near3 ablat\$3) with (via hole trench open\$3 groove recess) | USPAT; US-PGPUB | 2004/06/07 20:25 |
| - | 797 | ((laser near3 ablat\$3) with (via hole trench open\$3 groove recess)) and isolat\$3 | USPAT; US-PGPUB | 2004/06/07 20:25 |
| - | 517 | (((laser near3 ablat\$3) with (via hole trench open\$3 groove recess)) and isolat\$3) and (print\$3 writ\$3 inkjet ink-jet) | USPAT; US-PGPUB | 2004/06/07 20:44 |
| - | 2 | (device near3 isolat\$3) near20 (laser near5 ablat\$3) | USPAT; US-PGPUB | 2004/06/07 20:44 |
| | - | | | |